

Supplementary materials

Effect of Post-Thermal Annealing on the Performance and Charge Photogeneration Dynamics of PffBT4T-2OD/PC₇₁BM Solar Cells

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S1 Current density-voltage (J - V) curves of PffBT4T-2OD and PffBT4T-2OD:PC₇₁BM devices

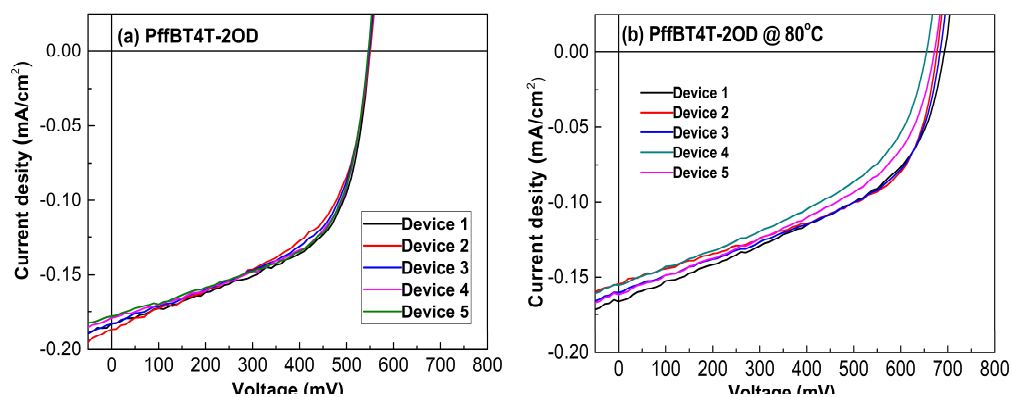


Figure S1. J - V curves of PffBT4T-2OD devices fabricated at indicated post thermal-annealing temperatures.

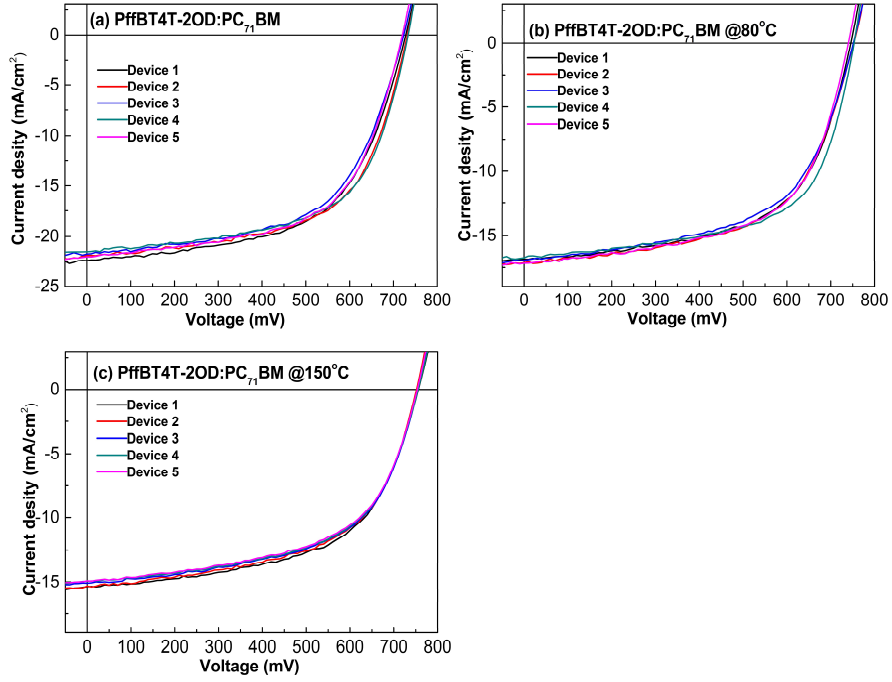


Figure S2. J - V curves of PffBT4T-2OD:PC₇₁BM devices fabricated at indicated post thermal-annealing temperatures.

S2 Fitting parameters of TRPL kinetics traces

Table ST1. Fitting parameters of TRPL kinetics traces in Figures 4.

Sample	Fitting parameters				
	A_1	τ_1 (ps)	A_2	τ_2 (ps)	$\bar{\tau}$ (ps) ^{a)}
Net PffBT4T-2OD	1	305			305
Unannealed PffBT4T-2OD/PC ₇₁ BM	0.34	8	0.66	43	31
80 °C annealed PffBT4T-2OD/PC ₇₁ BM	0.31	9	0.69	83	60
150 °C annealed PffBT4T-2OD/PC ₇₁ BM	0.27	9	0.73	96	72

a) $\bar{\tau} = \frac{A_1\tau_1 + A_2\tau_2}{A_1 + A_2}$

S3 TA kinetics under varies excitation fluencies

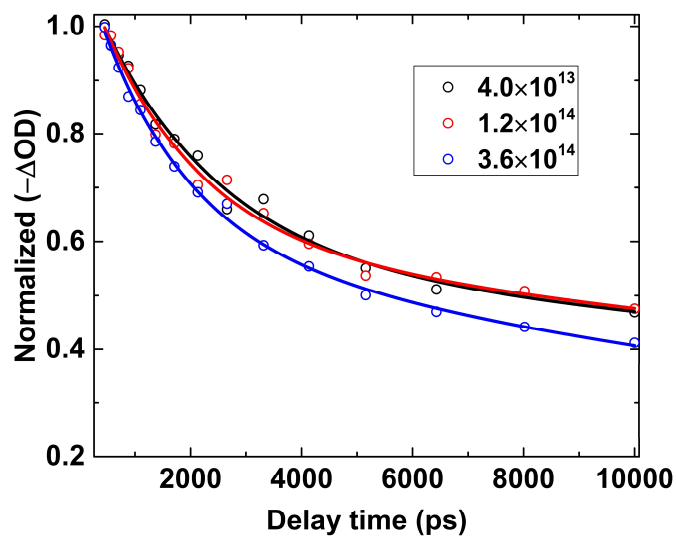


Figure S3. Normalized TA kinetics of 80 °C annealed PffBT4T-2OD:PC₇₁BM film after photoexcitation at 650 nm and probe at 700nm. The excitation fluences are 4.0×10^{13} , 1.2×10^{14} and 3.6×10^{14} photons/cm², respectively.

Table ST2. Fitting parameters of TA kinetics traces in Figure S3.

Sample	Fluence (photons/cm ²)	Fitting parameters			
		A_1	τ_1 (ns)	A_2	τ_2 (ns)
80 °C annealed PffBT4T- 2OD/PC ₇₁ BM	4.0×10^{13}	0.13	2.2	0.13	51
	1.2×10^{14}	0.10	1.8	0.11	42
	3.6×10^{14}	0.08	1.6	0.09	25